

**Amendments to the Claims:**

*This listing of claims will replace all prior versions, and listings, of claims in the application:*

**Listing of Claims:**

1. (Previously Presented) A semiconductor device comprising:  
an insulation film formed on a substrate;  
a buried metal interconnect formed in the insulation film; and  
a barrier metal film formed between the insulation film and the metal interconnect,  
wherein the barrier metal film is a metal oxide film, and  
wherein the metal oxide film contains at least one of the elements forming the insulation film and is made of at least one selected from a group consisting of Zr, Hf, W, V, Mo, Os, Rh, Ir, Pd and Pt or any alloy thereof.

2-5. (Canceled).

6. (Previously Presented) The semiconductor device of claim 1, wherein a metal forming the metal oxide film is a refractory metal.

7. (Original) The semiconductor device of claim 1, wherein the metal interconnect is formed of copper or an copper alloy.

8-53. (Cancelled).

54. (Previously Presented) The semiconductor device of claim 1, wherein the insulation film is SiO<sub>2</sub>, SiOF<sub>2</sub>, SiOC, SiON, SiOCN, or an organic film containing oxygen.

55. (Currently Amended) The semiconductor device of claim 1, wherein the insulation film is nitride, carbide or silicide.